TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

TLP3041(S),TLP3042(S),TLP3043(S)

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVER
SOLID STATE RELAY

The TOSHIBA TLP3041 (S), TLP3042 (S), TLP3043 (S) consist of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

• Peak Off-State Voltage : 400 V (min)

• Trigger LED Current : 15 mA (max) (TLP3041(S))

10 mA (max) (TLP3042(S)) 5 mA (max) (TLP3043(S))

On-State Current : 100 mA (max)
 Isolation Voltage : 5000 Vrms (min)

• UL Recognized : UL1577, File No. E67349

• SEMKO Approved : SS EN60065

SS EN60950, File No.9841109

BSI Approved : BS EN60065, File No.8385
 BS EN60950, File No.8386

Option (D4) type

VDE approved: DIN EN60747-5-2

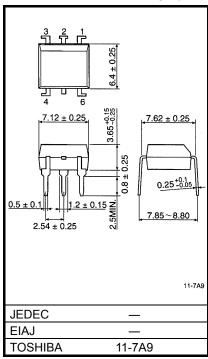
Approved No. 40009302

Maximum operating insulation voltage: 890 VpK Highest permissible over voltage: 8000 VpK

(Note):When a EN60747-5-2 approved type is needed, please designate the "Option (D4)"

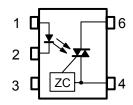
Construction mechanical rating

	7.62 mm pich Standard Type	10.16 mm pich TLPxxxxF Type		
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)		
Clearance	7.0 mm (Min)	8.0 mm (Min)		
Insulation Thickness	0.5 mm (Min)	0.5 mm (Min)		



weight: 0.39g

Pin Configuration (top view)



- 1: Anode
- 2: Cathode
- 3: N.C.
- 4:Terminal 1
- 6:Terminal 2

ZC:Zero-cross Circuit



Absolute Maximum Ratings (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT	
	Forward Current		lF	50	mA	
	Forward Current Derati (Ta ≥ 53°C)	ng	ΔI _F / °C	-0.7	mA / °C	
	Peak Forward Current (100 μs pulse, 100 pps)		I _{FP}	1	Α	
LED	Power Dissipation		P _D	100	mW	
	Power Dissipation Dera (Ta ≥ 25°C)	ating	ΔP _D / °C	-1.0	mW / °C	
	Reverse Voltage		V _R	5	V	
	Junction Temperature		Tj	125	°C	
	Off-State Output Termi	nal Voltage	V_{DRM}	400	V	
	On-Stage RMS	Ta = 25°C	I=	100	A	
DETECTOR	Current	Ta = 70°C	I _{T(RMS)}	50	- mA	
	On-State Current Dera (Ta ≥ 25°C)	ting	ΔI _T / °C	-1.1	mA / °C	
	Peak On-Stage Curren (100μs pulse, 120pps)	t	I _{TP}	2	А	
	Peak Nonrepetitive Sur Current (P _W = 10ms, D		I _{TSM}	1.2	Α	
	Power Dissipation		P_{D}	300	mW	
	Power Dissipation Derating (Ta ≥ 25°C)		ΔP _D / °C	-4.0	mW / °C	
	Junction Temperature		Tj	115	°C	
Stora	age Temperature Range		T _{stg}	−55 ~ 150	°C	
Operating Temperature Range			T _{opr}	−40 ~ 100	°C	
Lead Soldering Temperature (10s)			T _{sol}	260	°C	
Total Package Power Dissipation			PT	330	mW	
Total Package Power Dissipation Derating (Ta ≥ 25°C)			ΔP _T / °C	-4.4	mW / °C	
	tion Voltage 1 min., R.H. ≤ 60%)	BVS	5000	Vrms		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

Recommended Operating Conditions

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT
Supply Voltage	V _{AC}	_	_	120	Vac
Forward Current	l _F *	15	20	25	mA
Peak On-Stage Current	I _{TP}	_	_	1	Α
Operating Temperature	T _{opr}	-25		85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

*: In the case of TLP3042



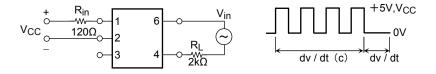
Individual Electrical Characteristics (Ta = 25°C)

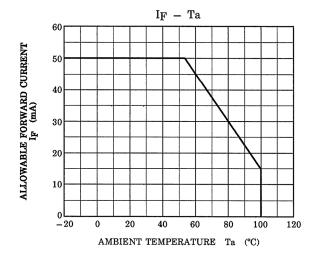
	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
	Forward Voltage	V _F	I _F = 10mA	1.0	1.15	1.3	V
LED	Reverse Current	I _R	V _R = 5V	_	_	10	μА
	Capacitance	C _T	V = 0, f = 1MHz	_	10	_	pF
	Peak Off-State Current	I _{DRM}	V _{DRM} = 400V	_	10	100	nA
~	Peak On-Stage Voltage	V _{TM}	I _{TM} = 100mA	_	1.7	3.0	V
CTO	Holding Current	lΗ	_	_	0.6	_	mA
DETECTOR	Critical Rate of Rise of Off- State Voltage	dv / dt	V _{in} = 120Vrms, Ta = 85°C (Fig.1)	200	500	_	V / μs
	Critical Rate of Rise of Commutating Voltage	dv / dt(c)	V _{in} = 30Vrms, IT = 15mA (Fig.1)		0.2	_	V / μs

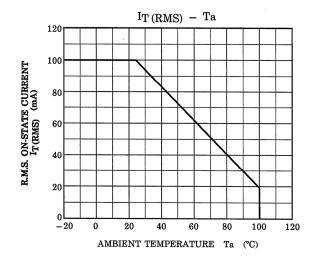
Coupled Electrical Characteristics (Ta = 25°C)

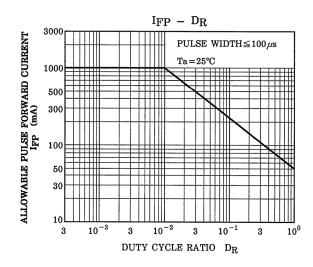
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Trigger LED Current	TLP3041(S)	I _{FT}	V _T = 3V	_	_	15	mA
	TLP3042(S)			_	5	10	
	TLP3043(S)			_	_	5	
Inhibit Voltage		V _{IH}	I _F = Rated I _{FT}	_	_	40	V
Leakage in Inhibited State		I _{IH}	I _F = Rated I _{FT} V _T = Rated V _{DRM}	_	100	300	μА
Capacitance Input to Out			0.8	_	pF		
Isolation Resistance		R _S	V _S = 500V (R.H. ≤ 60%)	5×10 ¹⁰	10 ¹⁴	_	Ω
			AC, 1 minute	5000	_	_	Vrms
Isolation Voltage		BVS	AC, 1 second (in oil)	_	10000	_	VIIIS
			DC, 1 minute (in oil)	_	10000	_	Vdc

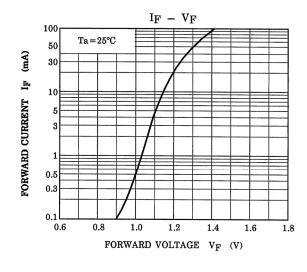
Fig. 1 dv / dt test circuit

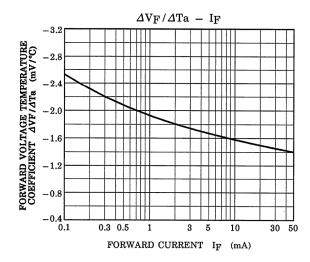


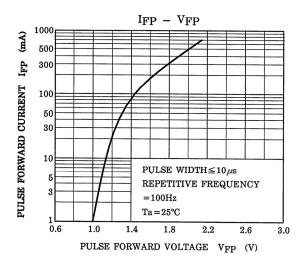


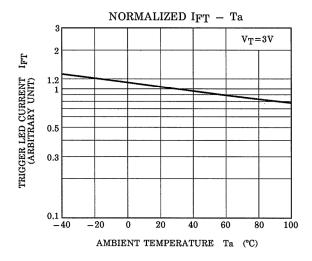


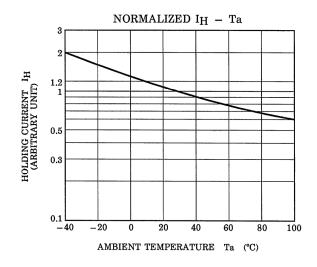


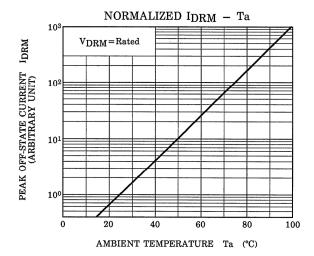


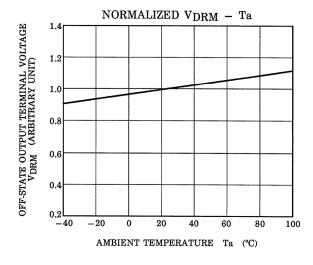


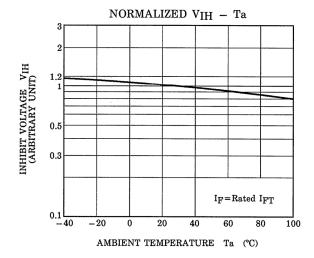


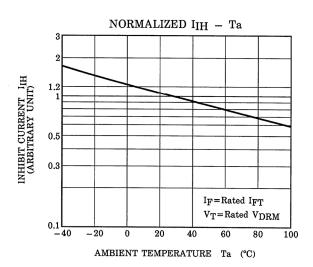












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